

7MBP200VEA120-50

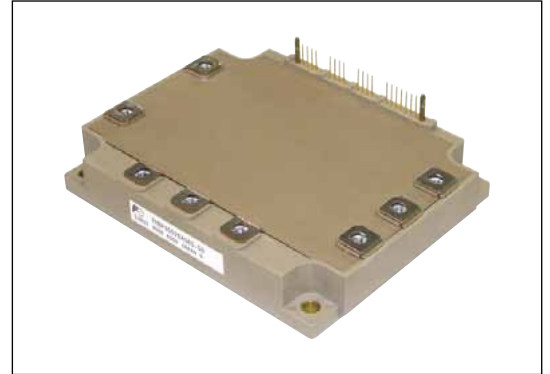
IGBT Modules

IGBT MODULE (V series)

1200V / 200A / IPM

■ Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings ($T_c=25^\circ\text{C}$, $V_{cc}=15\text{V}$ unless otherwise specified)

Items	Symbol	Min.	Max.	Units		
Collector-Emitter Voltage (*1)	V_{CES}	0	1200	V		
Short Circuit Voltage	V_{SC}	400	800	V		
Inverter	Collector Current	DC	I_C	-	200	A
		1ms	I_{cp}	-	400	A
		Duty=100% (*2)	$-I_C$	-	200	A
Collector Power Dissipation	1 device (*3)	P_C	-	961	W	
Brake	Collector Current	DC	I_C	-	100	A
		1ms	I_{cp}	-	200	A
	Forward Current of Diode		I_F	-	100	A
	Collector Power Dissipation	1 device (*3)	P_C	-	581	W
Supply Voltage of Pre-Driver (*4)	V_{CC}	-0.5	20	V		
Input Signal Voltage (*5)	V_{in}	-0.5	$V_{CC}+0.5$	V		
Alarm Signal Voltage (*6)	V_{ALM}	-0.5	V_{CC}	V		
Alarm Signal Current (*7)	I_{ALM}	-	20	mA		
Junction Temperature	T_J	-	150	$^\circ\text{C}$		
Operating Case Temperature	T_{opr}	-20	110	$^\circ\text{C}$		
Storage Temperature	T_{stg}	-40	125	$^\circ\text{C}$		
Solder Temperature (*8)	T_{sol}	-	260	$^\circ\text{C}$		
Isolating Voltage (*9)	V_{iso}	-	AC2500	Vrms		
Screw Torque	Terminal (M5)	-	-	-		
	Mounting (M5)	-	-	3.5	Nm	

Note *1: V_{CES} shall be applied to the input voltage between all Collector and Emitter. [P1- (U, V, W, B), P2- (U, V, W, B), (U, V, W, B)-N1, (U, V, W, B)-N2]

Note *2: Duty=125 $^\circ\text{C}/R_{th(j-c)}$ / ($I_F \times V_F$ Max.) $\times 100$

Note *3: $P_C=125^\circ\text{C}/R_{th(j-c)}$ (Inverter & Brake)

Note *4: V_{CC} shall be applied to the input voltage between terminal No.3 and 1, 7 and 5, 11 and 9, 14 and 13.

Note *5: V_{in} shall be applied to the input voltage between terminal No.2 and 1, 6 and 5, 10 and 9, 15~18 and 13.

Note *6: V_{ALM} shall be applied to the voltage between terminal No.4 and 1, 8 and 5, 12 and 9, 19 and 13.

Note *7: I_{ALM} shall be applied to the input current to terminal No.4, 8, 12 and 19.

Note *8: Immersion time 10 \pm 1 sec. 1 time.

Note *9: Terminal to base, 50/60Hz sine wave 1 min. All terminals should be connected together during the test.

● Electrical Characteristics ($T_J=25^\circ\text{C}$, $V_{CC}=15\text{V}$ unless otherwise specified)

Items	Symbol	Conditions	Min.	Typ.	Max.	Units		
Inverter	Collector Current at off signal input	I_{CES}	$V_{CE}=1200\text{V}$		-	-	1.0	mA
	Collector-Emitter saturation voltage (*10)	$V_{CE(sat)}$	$I_C=200\text{A}$	Terminal	-	-	2.30	V
				Chip	-	1.70	-	V
	Forward voltage of FWD (*10)	V_F	$I_F=200\text{A}$	Terminal	-	-	2.75	V
Chip				-	2.10	-	V	
Brake	Collector Current at off signal input	I_{CES}	$V_{CE}=1200\text{V}$		-	-	1.0	mA
	Collector-Emitter saturation voltage (*10)	$V_{CE(sat)}$	$I_C=100\text{A}$	Terminal	-	-	2.20	V
				Chip	-	1.70	-	V
	Forward voltage of FWD (*10)	V_F	$I_F=100\text{A}$	Terminal	-	-	2.85	V
Chip				-	2.35	-	V	
Switching time	t_{on}	$V_{DC}=600\text{V}$, $T_J=125^\circ\text{C}$, $I_C=200\text{A}$		1.1	-	-	μs	
	t_{off}			-	-	2.1	μs	
	t_{rr}	$V_{DC}=600\text{V}$, $I_F=200\text{A}$		-	-	0.3	μs	
Supply current of P-side pre-driver (per one unit)	I_{ccp}	Switching Frequency= 0-15kHz		-	-	42	mA	
Supply current of N-side pre-driver	I_{ccn}	$T_C=-20\sim 110^\circ\text{C}$		-	-	142	mA	
Input signal threshold voltage	$V_{in(th)(on)}$	$V_{in}-\text{GND}$	ON	1.2	1.4	1.6	V	
	$V_{in(th)(off)}$		OFF	1.5	1.7	1.9	V	
Over Current Protection Level	Inverter	I_{OC}	$T_J=125^\circ\text{C}$	300	-	-	A	
				Brake	150	-	-	A
Over Current Protection Delay time	t_{dOC}	$T_J=125^\circ\text{C}$		-	5	-	μs	
Short Circuit Protection Delay time	t_{sc}	$T_J=125^\circ\text{C}$		-	2	3	μs	
IGBT Chips Over Heating Protection Temperature Level	$T_{J(OH)}$	Surface of IGBT Chips		150	-	-	$^\circ\text{C}$	
Over Heating Protection Hysteresis	T_{JH}			-	20	-	$^\circ\text{C}$	
Under Voltage Protection Level	V_{UV}			11.0	-	12.5	V	
Under Voltage Protection Hysteresis	V_H			0.2	0.5	-	V	
Alarm Signal Hold Time	$t_{ALM(OC)}$	ALM-GND	$T_C=-20\sim 110^\circ\text{C}$	$V_{CC}\geq 10\text{V}$	1.0	2.0	2.4	ms
	$t_{ALM(UV)}$				2.5	4.0	4.9	ms
	$t_{ALM(T_{J(OH)})}$				5.0	8.0	11.0	ms
Resistance for current limit	R_{ALM}			960	1265	1570	Ω	

Note *10: The Max value is a case where it measures from P2- (U, V, W, B), (U, V, W, B)-N2.

● Thermal Characteristics ($T_c = 25^\circ\text{C}$)

Items	Symbol	Min.	Typ.	Max.	Units		
Junction to Case Thermal Resistance (*11)	Inverter	IGBT	$R_{th(j-c)Q}$	-	-	0.130	$^\circ\text{C}/\text{W}$
		FWD	$R_{th(j-c)D}$	-	-	0.195	$^\circ\text{C}/\text{W}$
	Brake	IGBT	$R_{th(j-c)Q}$	-	-	0.215	$^\circ\text{C}/\text{W}$
		FWD	$R_{th(j-c)D}$	-	-	0.400	$^\circ\text{C}/\text{W}$
Case to Fin Thermal Resistance with Compound	$R_{th(c-f)}$	-	0.05	-	$^\circ\text{C}/\text{W}$		

Note *11: For 1device, the measurement point of the case is just under the chip.

● Noise Immunity ($V_{DC}=600\text{V}$, $V_{CC}=15\text{V}$)

Items	Conditions	Min.	Typ.	Max.	Units
Common mode rectangular noise	Pulse width $1\mu\text{s}$, polarity \pm , 10 min. Judge : no over-current, no miss operating	± 2.0	-	-	kV

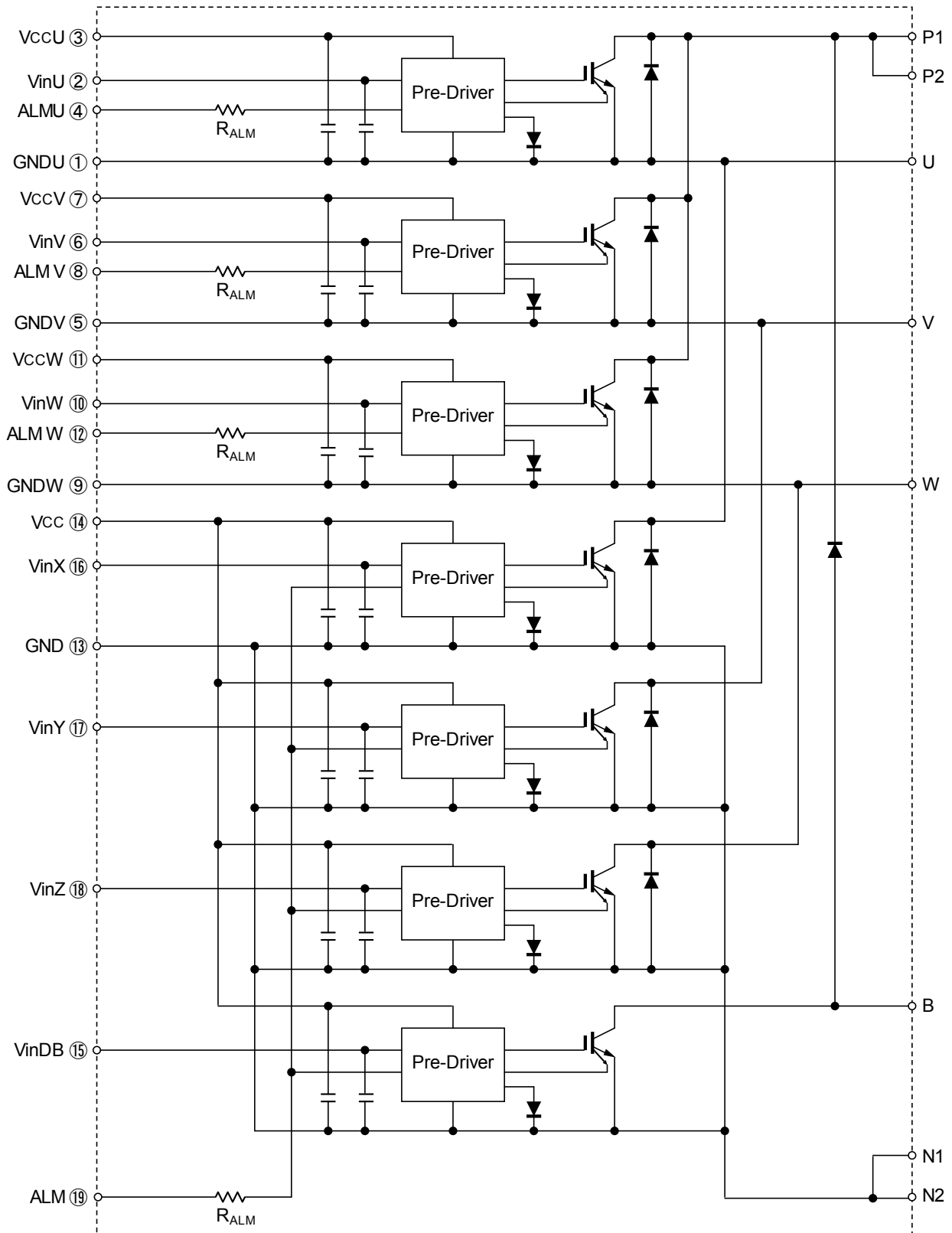
● Recommended Operating Conditions

Items	Symbol	Min.	Typ.	Max.	Units
DC Bus Voltage	V_{DC}	-	-	800	V
Power Supply Voltage of Pre-Driver	V_{CC}	13.5	15.0	16.5	V
Switching frequency of IPM	f_{sw}	-	-	20	kHz
Arm shoot through blocking time for IPM's input signal	t_{dead}	1.0	-	-	μs
Screw Torque (M5)	-	2.5	-	3.5	Nm

● Weight

Items	Symbol	Min.	Typ.	Max.	Units
Weight	Wt	-	940	-	g

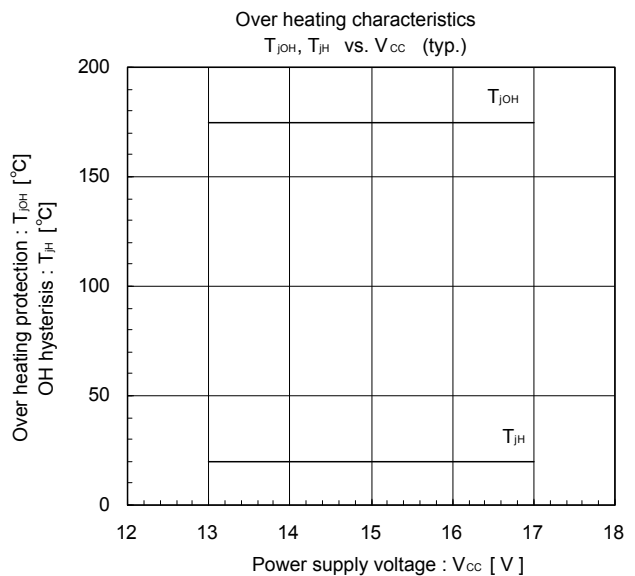
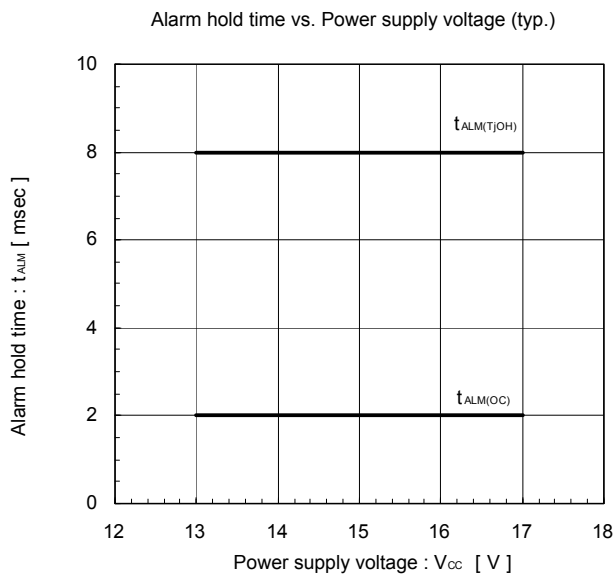
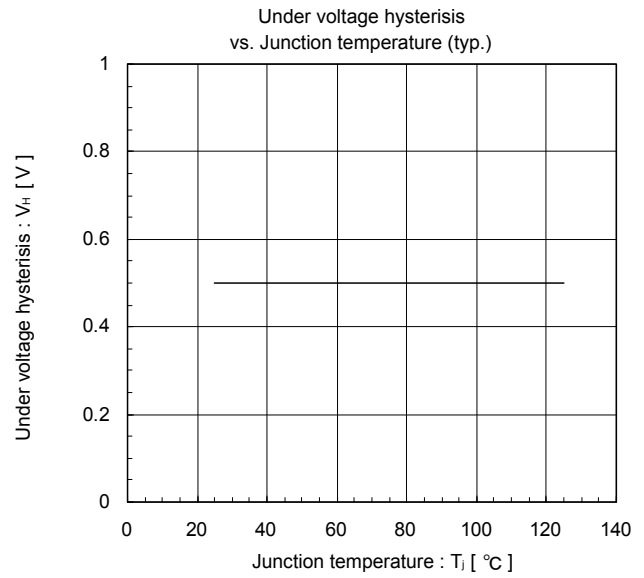
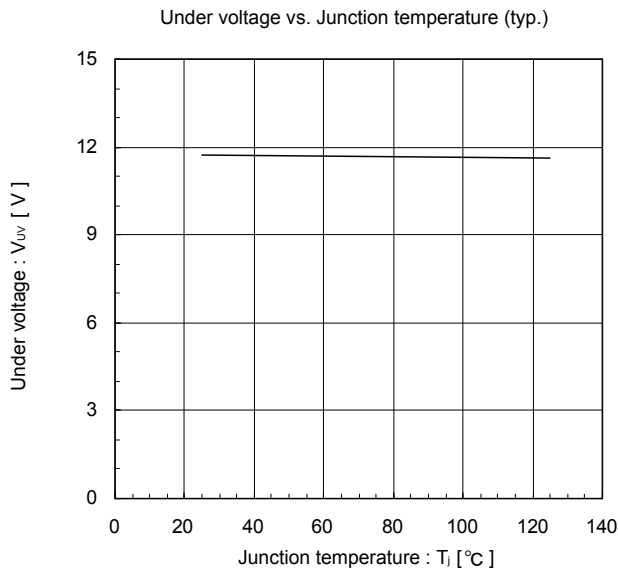
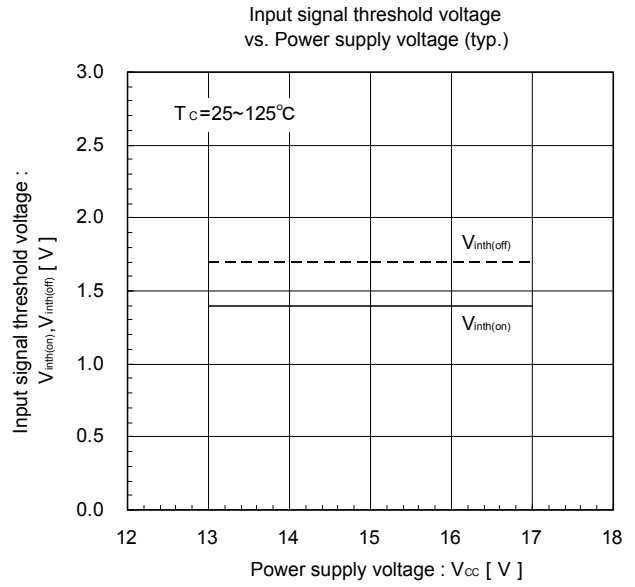
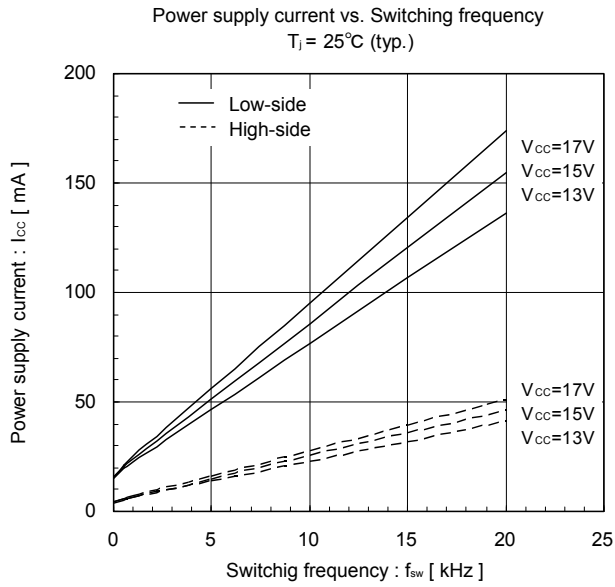
■ Block Diagram



Pre-drivers include following functions

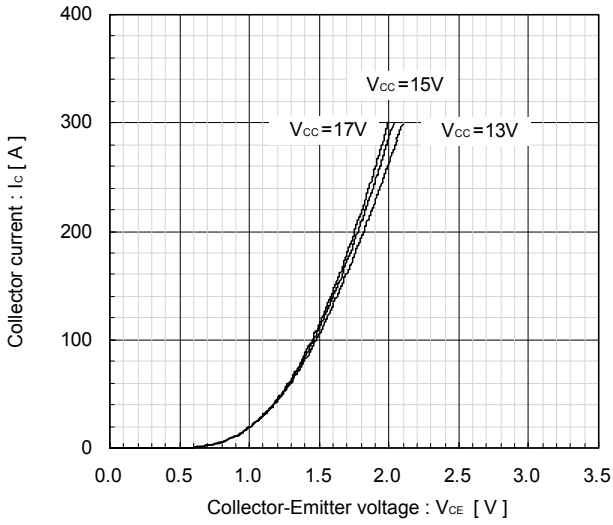
1. Amplifier for driver
2. Short circuit protection
3. Under voltage lockout circuit
4. Over current protection
5. IGBT chip over heating protection

■ Characteristics (Representative)

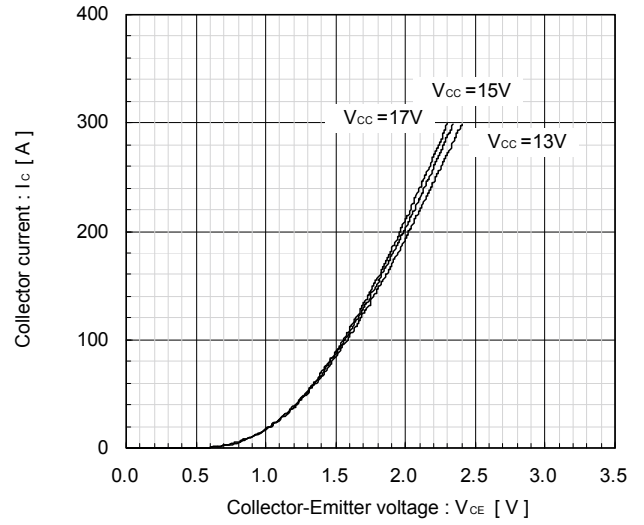


Inverter

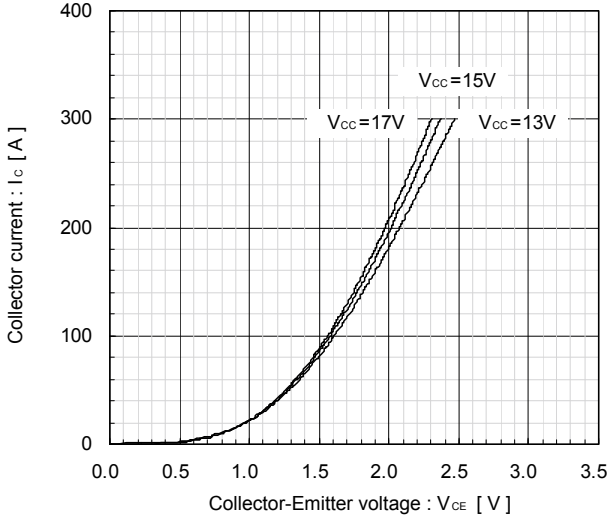
Collector current vs. Collector-Emitter voltage
 $T_j = 25^\circ\text{C}$ [Chip] (typ.)



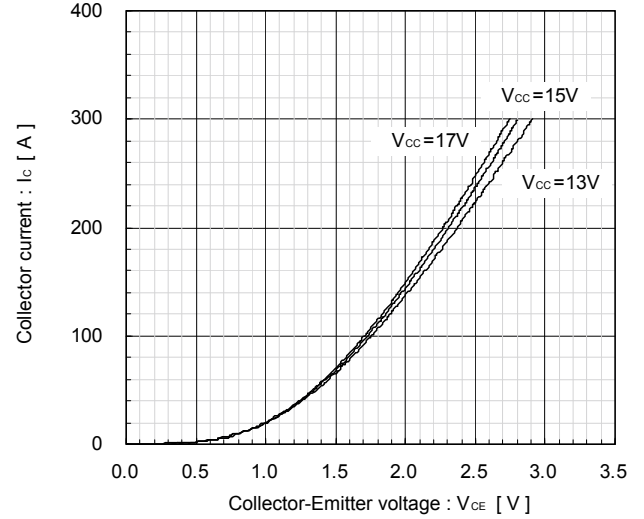
Collector current vs. Collector-Emitter voltage
 $T_j = 25^\circ\text{C}$ [Terminal] (typ.)



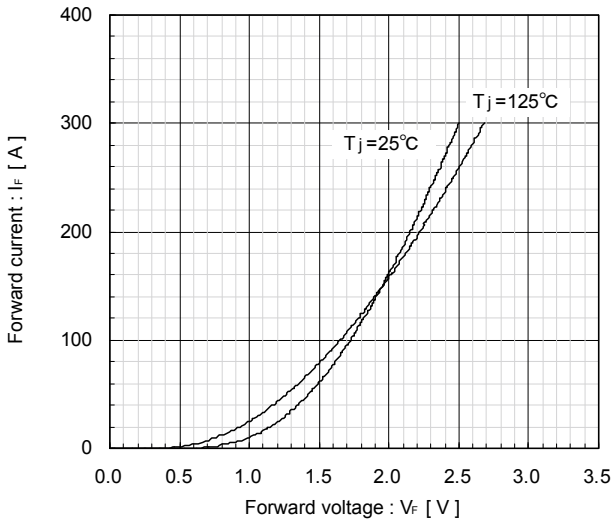
Collector current vs. Collector-Emitter voltage
 $T_j = 125^\circ\text{C}$ [Chip] (typ.)



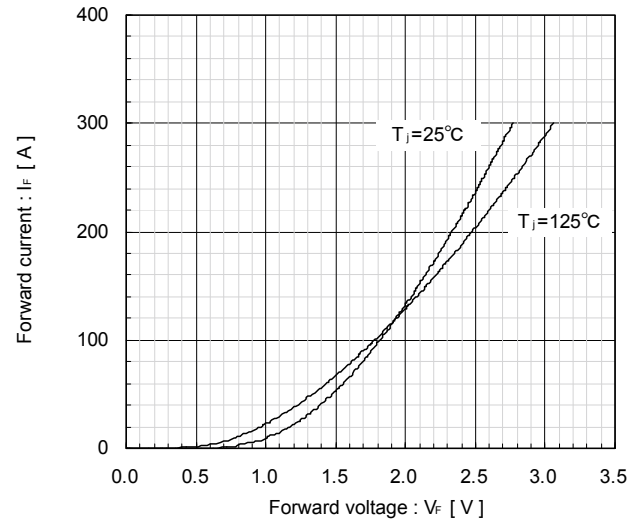
Collector current vs. Collector-Emitter voltage
 $T_j = 125^\circ\text{C}$ [Terminal] (typ.)



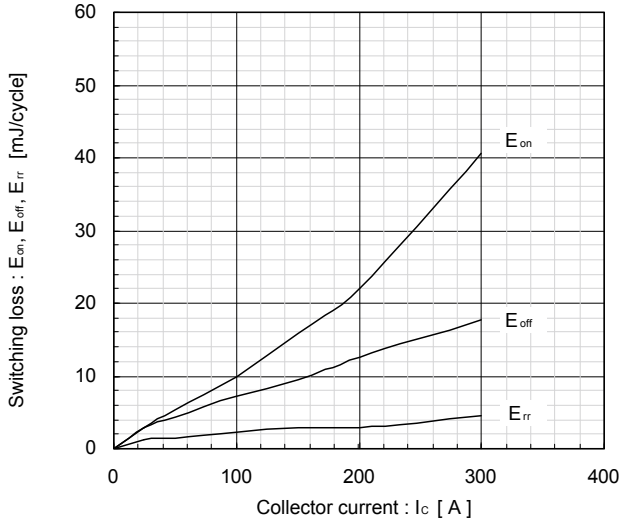
Forward current vs. Forward voltage
 [Chip] (typ.)



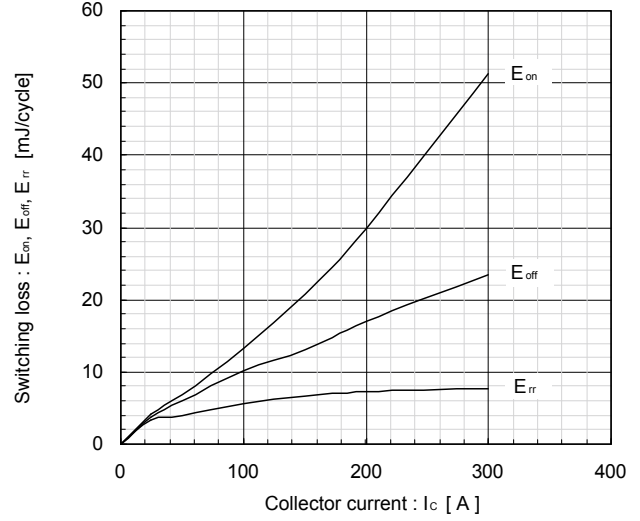
Forward current vs. Forward voltage
 [Terminal] (typ.)



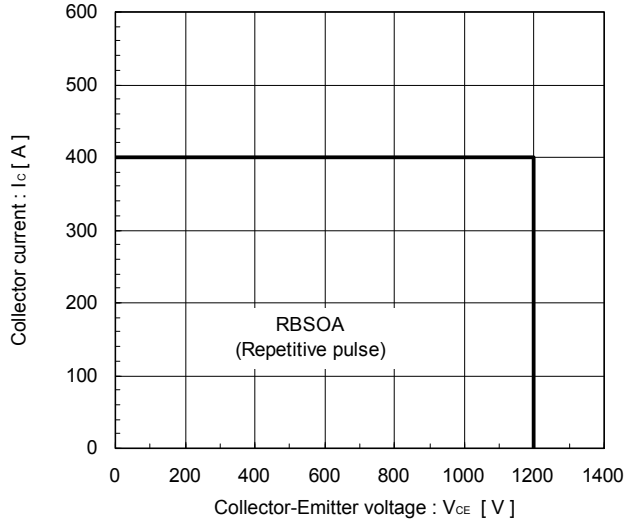
Switching Loss vs. Collector Current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=25^{\circ}C$



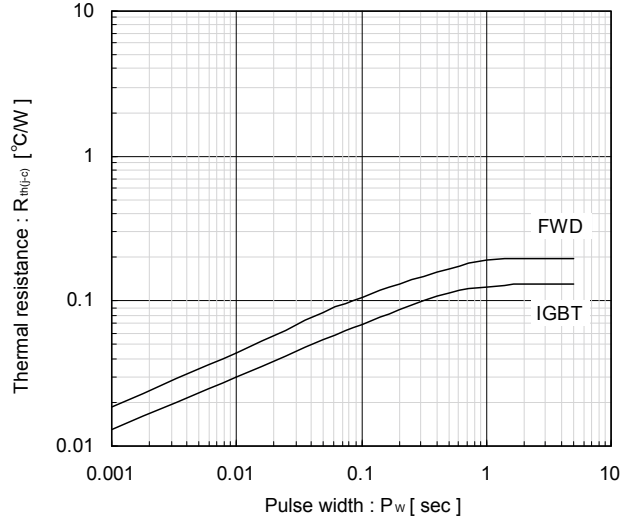
Switching Loss vs. Collector Current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_J=125^{\circ}C$



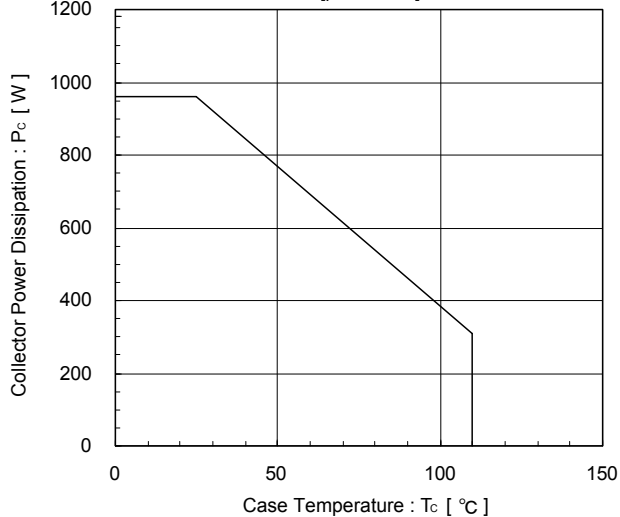
Reversed biased safe operating area
 $V_{CC}=15V, T_J \leq 125^{\circ}C$ [Main Terminal] (min.)



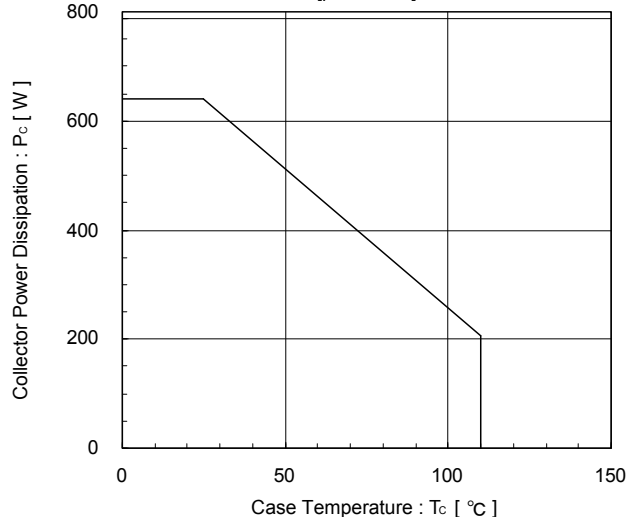
Transient thermal resistance (max.)



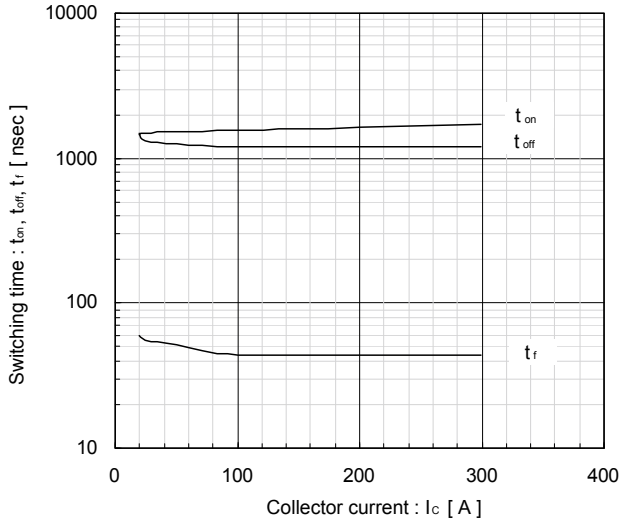
Power derating for IGBT (max.)
 [per device]



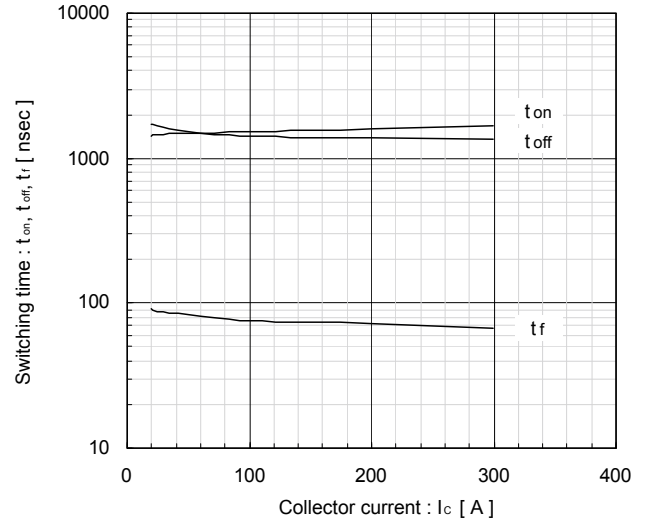
Power derating for FWD (max.)
 [per device]



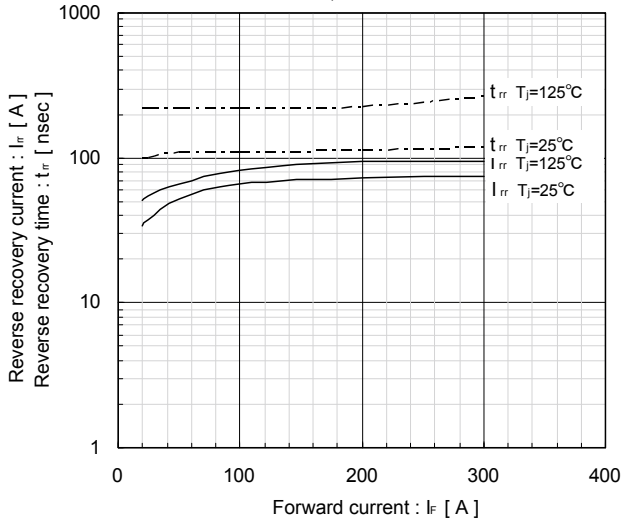
Switching time vs. Collector current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_j=25^\circ C$



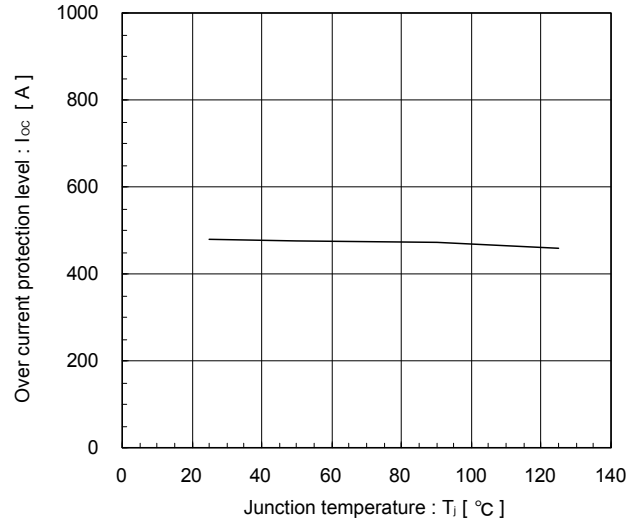
Switching time vs. Collector current (typ.)
 $V_{DC}=600V, V_{CC}=15V, T_j=125^\circ C$



Reverse recovery characteristics (typ.)
 t_{rr}, I_{rr} vs. I_f

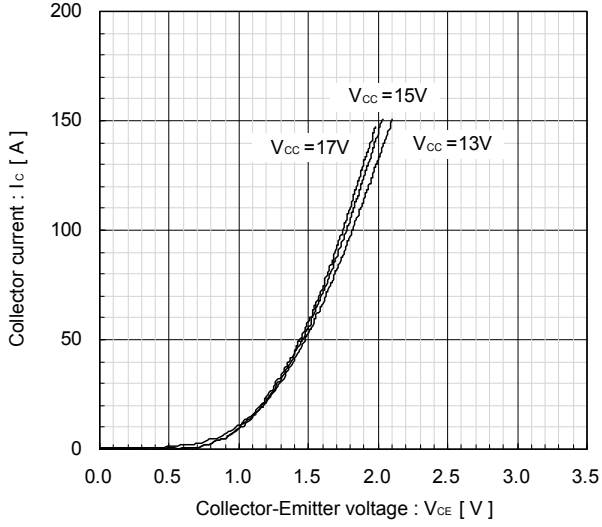


Over current protection vs. Junction temperature (typ.)
 $V_{CC}=15V$

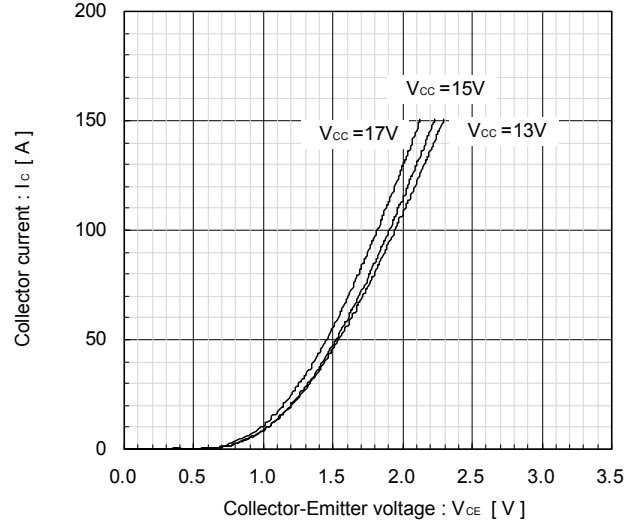


Brake

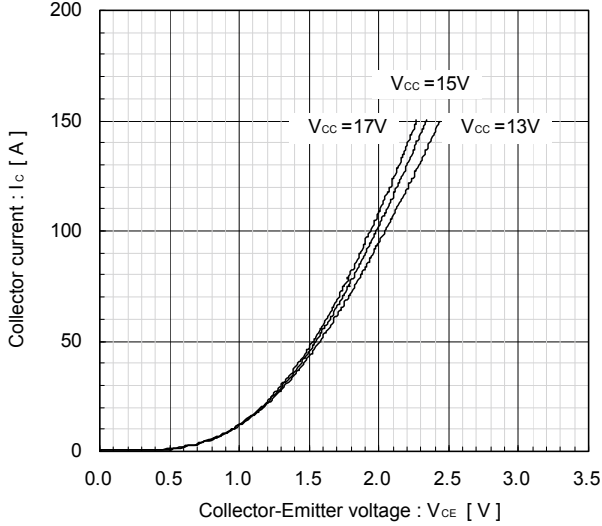
Collector current vs. Collector-Emitter voltage
 $T_j = 25^\circ\text{C}$ [Chip] (typ.)



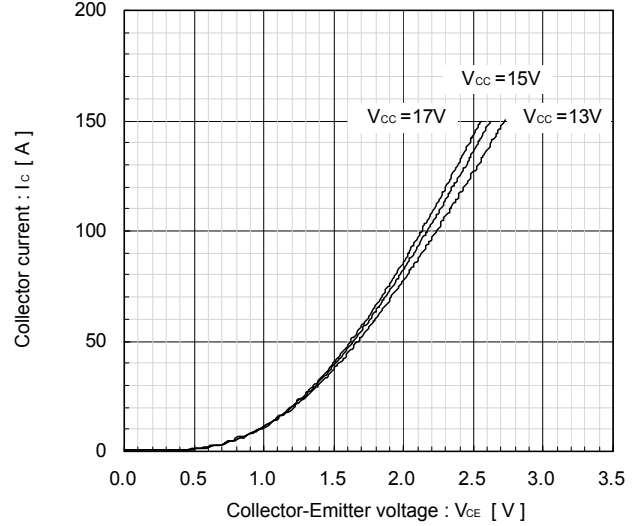
Collector current vs. Collector-Emitter voltage
 $T_j = 25^\circ\text{C}$ [Terminal] (typ.)



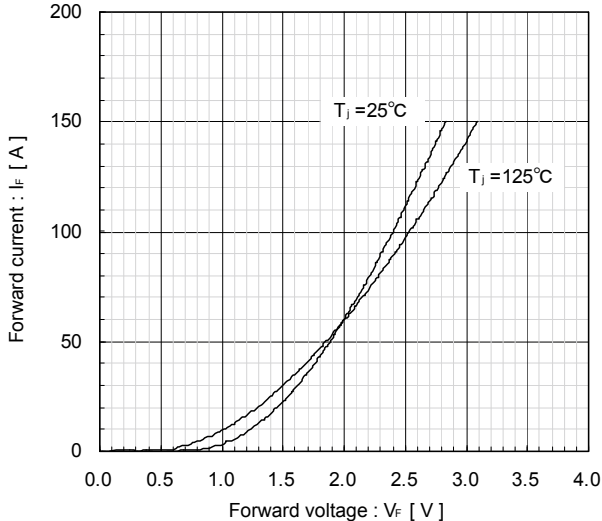
Collector current vs. Collector-Emitter voltage
 $T_j = 125^\circ\text{C}$ [Chip] (typ.)



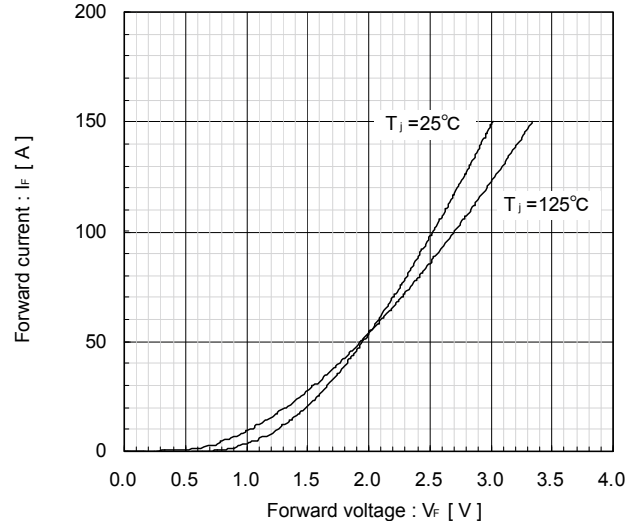
Collector current vs. Collector-Emitter voltage
 $T_j = 125^\circ\text{C}$ [Terminal] (typ.)

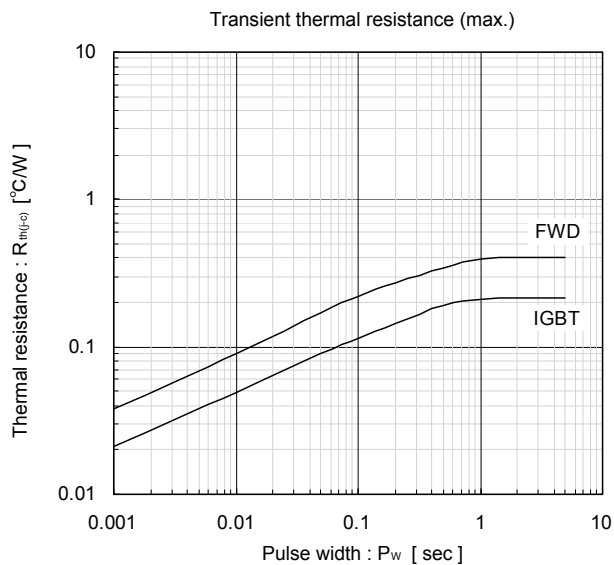
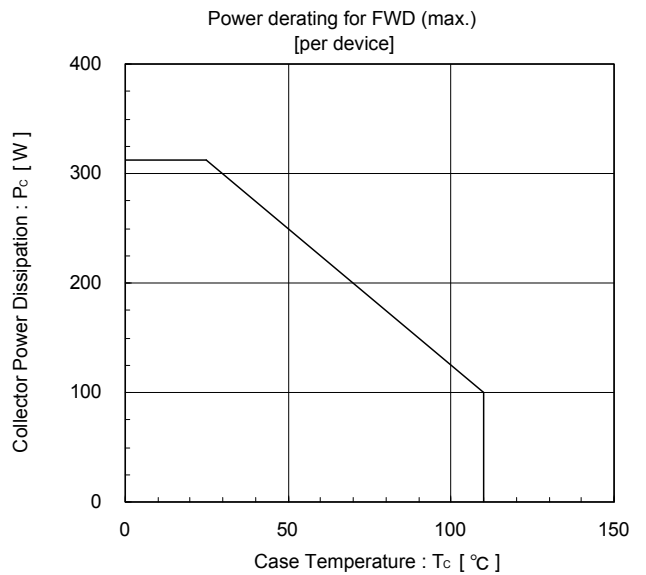
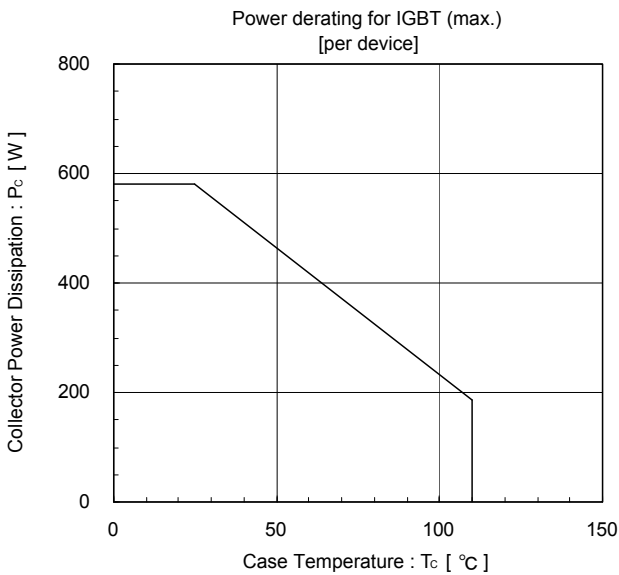
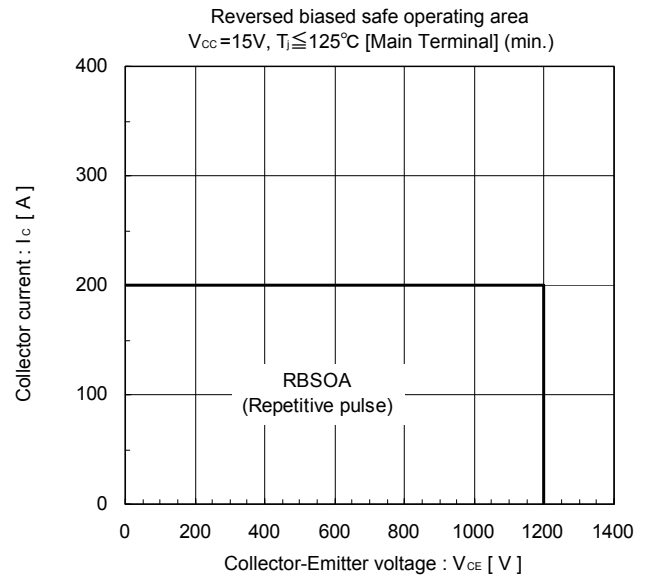
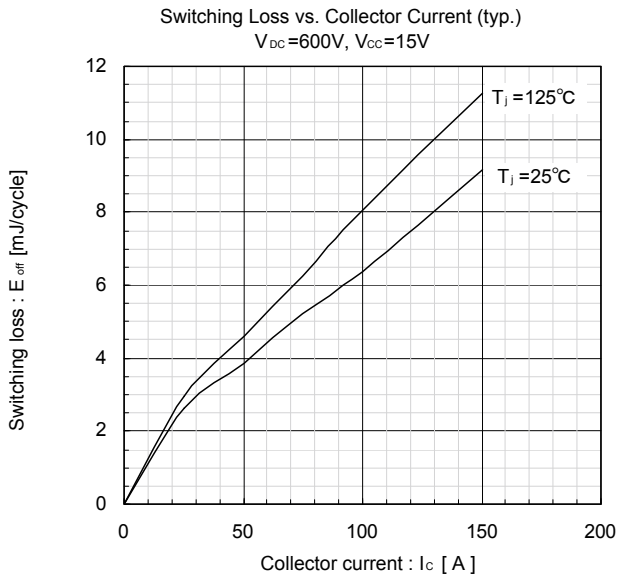


Forward current vs. Forward voltage
 [Chip] (typ.)

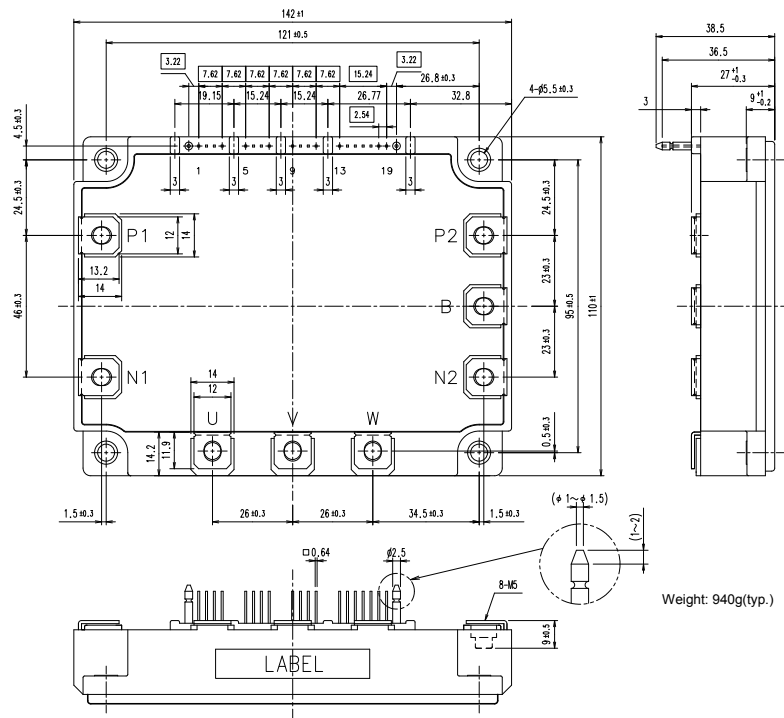


Forward current vs. Forward voltage
 [Terminal] (typ.)





■ Outline Drawings, mm



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IGBT Modules

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4 技术资料	www.fujielectric.com.cn/products/semiconductor/model/igbt/technical/
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6 IGBT 损耗模拟软件	www.fujielectric.com.cn/products/semiconductor/model/igbt/simulation/
7 AT-NPC 3-Level 损耗模拟软件	www.fujielectric.com.cn/products/semiconductor/model/igbt/simulation_3level/
8 富士电机技报	www.fujielectric.com.cn/products/semiconductor/journal/
9 产品咨询	www.fujielectric.com.cn/products/semiconductor/contact/
10 产品更改和停产信息	www.fujielectric.com.cn/products/semiconductor/discontinued/